



# 《风光欣》技术资料

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## C945

### NPN EPITAXIAL SILICON TRANSISTOR

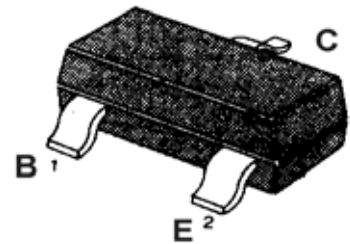
\*Complement to A733

\*Collector-Base Voltage  $V_{CB0}=60V$

#### ABSOLUTE MAXIMUM RATINGS( $T_A=25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	50	V
Emitter -Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_c$	150	mA
Collector Dissipation	$P_c$	200	mW
Junction Temperature	$T_J$	150	

SOT-23



#### ELECTRICAL CHARACTERISTICS( $T_A=25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CB0}$	$I_c=100 \mu A, I_E=0$	60			V
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	$I_c=10mA, I_B=0$	50			V
Emitter-Base Breakdown Voltage	$BV_{EBO}$	$I_E=10 \mu A, I_c=0$	5			V
Collector Cut-off Current	$I_{CB0}$	$V_{CB}=40V, I_E=0$			0.1	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=3V, I_c=0$			0.1	$\mu A$
DC Current Gain	$H_{FE}$	$V_{CE}=6V, I_c=1.0mA$	40		700	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_c=100mA, I_B=10mA$		0.15	0.3	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE}=6V, I_c=10mA$		250		MHz
Output Capacitance	$C_{OB}$	$V_{CB}=6V, I_E=0, F=1MHz$		3	4	pF

#### Hfe CLASSIFICATION

Classification	R	O	Y	G	L
HFE	40-80	70-140	120-240	200-400	350-700